## Level shifting techniques in $\mathrm{I}^{2} \mathrm{C}$-bus design

Rev. 01 - 18 June 2007

Document information

| Info | Content |
| :--- | :--- |
| Keywords | I2C-bus, level shifting |
| Abstract | Logic level shifting may be required when interfacing legacy devices with <br> newer devices that use a smaller geometry process. For bidirectional bus <br> systems like the I ${ }^{2}$ C-bus, such a level shifter must also be bidirectional, <br> without the need of a direction control signal. The simplest way to solve <br> this problem is by connecting a discrete MOS-FET to each bus line. |



Revision history

| Rev | Date | Description |
| :--- | :--- | :--- |
| 01 | 20070618 | Application note; initial version. |

## Contact information

For additional information, please visit: http://www.nxp.com
For sales office addresses, please send an email to: salesaddresses@nxp.com
AN10441_1

## 1. Introduction

Present technology processes for integrated circuits with clearances of $0.5 \mu \mathrm{~m}$ and less limit the maximum supply voltage and consequently the logic levels for the digital I/O signals. To interface these lower voltage circuits with existing 5 V devices, a level shifter is needed. For bidirectional bus systems like the $\mathrm{I}^{2} \mathrm{C}$-bus, such a level shifter must also be bidirectional, without the need of a direction control signal. The simplest way to solve this problem is by connecting a discrete MOS-FET to each bus line.

## 2. Bidirectional level shifter for Fast-mode and Standard-mode $I^{2} \mathrm{C}$-bus systems

In spite of its surprising simplicity, such a solution not only fulfils the requirement of bidirectional level shifting without a direction control signal, it also:

- isolates a powered-down bus section from the rest of the bus system
- protects the 'lower voltage' side against high voltage spikes from the 'higher-voltage' side.

The bidirectional level shifter can be used for both Standard-mode (up to100 kbit/s) or in Fast-mode (up to $400 \mathrm{kbit} / \mathrm{s}$ ) $\mathrm{I}^{2} \mathrm{C}$-bus systems. It is not intended for Hs-mode systems, which may have a bridge with a level shifting possibility.

### 2.1 Connecting devices with different logic levels

Different voltage devices could be connected to the same bus by using pull-up resistors to the supply voltage line. Although this is the simplest solution, the lower voltage devices must be 5 V tolerant, which can make them more expensive to manufacture. By using a bidirectional level shifter, however, it is possible to interconnect two sections of an $I^{2} \mathrm{C}$-bus system, with each section having a different supply voltage and different logic levels. Such a configuration is shown in Figure 1. The left 'low-voltage' section has pull-up resistors and devices connected to a 3.3 V supply voltage; the right 'high-voltage' section has pull-up resistors and devices connected to a 5 V supply voltage. The devices of each section have I/Os with supply voltage related logic input levels and an open-drain output configuration.

The level shifter for each bus line is identical and consists of one discrete N -channel enhancement MOS-FET; TR1 for the serial data line SDA and TR2 for the serial clock line SCL. The gates ( g ) have to be connected to the lowest supply voltage $\mathrm{V}_{\mathrm{DD} 1}$, the sources (s) to the bus lines of the 'lower-voltage' section, and the drains (d) to the bus lines of the 'higher-voltage' section. Many MOS-FETs have the substrate internally connected with its source, if this is not the case, an external connection should be made. Each MOS-FET has an integral diode ( $n$ - $p$ junction) between the drain and substrate.


Fig 1. Bidirectional level shifter circuit connecting two different voltage sections in an $I^{2} \mathrm{C}$-bus system

### 2.1.1 Operation of the level shifter

The following three states should be considered during the operation of the level shifter:

1. No device is pulling down the bus line. The bus line of the 'lower-voltage' section is pulled up by its pull-up resistors $R_{p}$ to 3.3 V . The gate and the source of the MOS-FET are both at 3.3 V , so its $\mathrm{V}_{\mathrm{GS}}$ is below the threshold voltage and the MOS-FET is not conducting. This allows the bus line at the 'higher-voltage' section to be pulled up by its pull-up resistor $R_{p}$ to 5 V . So the bus lines of both sections are HIGH, but at a different voltage level.
2. A 3.3 V device pulls down the bus line to a LOW level. The source of the MOS-FET also becomes LOW, while the gate stays at 3.3 V . $\mathrm{V}_{\mathrm{GS}}$ rises above the threshold and the MOS-FET starts to conduct. The bus line of the 'higher-voltage' section is then also pulled down to a LOW level by the 3.3 V device via the conducting MOS-FET. So the bus lines of both sections go LOW to the same voltage level.
3. A 5 V device pulls down the bus line to a LOW level. The drain-substrate diode of the MOS-FET the 'lower-voltage' section is pulled down until $\mathrm{V}_{\mathrm{GS}}$ passes the threshold and the MOS-FET starts to conduct. The bus line of the 'lower-voltage' section is then further pulled down to a LOW level by the 5 V device via the conducting MOS-FET. So the bus lines of both sections go LOW to the same voltage level.

The three states show that the logic levels are transferred in both directions of the bus system, independent of the driving section. State 1 performs the level shift function. States 2 and 3 perform a 'wired-AND' function between the bus lines of both sections as required by the $\mathrm{I}^{2} \mathrm{C}$-bus specification.

Supply voltages other than 3.3 V for $\mathrm{V}_{\mathrm{DD} 1}$ and 5 V for $\mathrm{V}_{\mathrm{DD} 2}$ can also be applied, e.g., 2 V for $V_{D D 1}$ and 10 V for $\mathrm{V}_{\mathrm{DD} 2}$ is feasible. In normal operation $\mathrm{V}_{\mathrm{DD} 2}$ must be equal to or higher than $\mathrm{V}_{\mathrm{DD} 1}$ ( $\mathrm{V}_{\mathrm{DD} 2}$ is allowed to fall below $\mathrm{V}_{\mathrm{DD1}}$ during switching power on/off).

## 3. Abbreviations

Table 1. Abbreviations

| Acronym | Description |
| :--- | :--- |
| $I^{2}$ C-bus | Inter-Integrated Circuit bus |
| I/O | Input/Output |
| FET | Field-Effect Transistor |
| MOS | Metal-Oxide Semiconductor |

## 4. Legal information

### 4.1 Definitions

Draft - The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

### 4.2 Disclaimers

General - Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes - NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use - NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of a NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.
Applications - Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

### 4.3 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.
$1^{2} \mathbf{C}$-bus - logo is a trademark of NXP B.V.

## 5. Contents

1 Introduction ..... 3
2 Bidirectional level shifter for Fast-mode and Standard-mode $\mathrm{I}^{2} \mathrm{C}$-bus systems ..... 3
2.1 Connecting devices with different logic levels ..... 3
2.1.1 Operation of the level shifter ..... 4
3 Abbreviations. ..... 5
4 Legal information ..... 6
Definitions ..... 6
4.2 Disclaimers ..... 6
4.3 Trademarks ..... 6
5 Contents ..... 7

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components
Click to view similar products for nxp manufacturer:
Other Similar products are found below :
MC13211R2 PCA9518PW,112 LFSTBEB865X MC33399PEFR2 PCA9551PW,112 MC34825EPR2 CBTW28DD14AETJ PCF8583P MC68340AB16E MC8640DTVJ1250HE EVBCRTOUCH MC9S08PT16AVLC MC9S08PT8AVTG MC9S08SH32CTL MCF54415CMJ250 MCIMX6Q-SDB MCIMX6SX-SDB 74ALVC125BQ,115 74HC4050N 74HC4514N MK21FN1M0AVLQ12 MKV30F128VFM10 FRDMK66F FRDM-KW40Z FRDM-MC-LVBLDC PESD18VF1BSFYL PMF63UNEX PSMN4R0-60YS, 115 HEF4028BPN RAPPID-567XFSW MPC565MVR56 MPC574XG-176DS MPC8548VJAUJD MPC860PCVR66D4 BT137-600E BT137S-600D.115 BT138-600E.127 BT139X600.127 BT258-600R. 127 BUK7628-100A118 BUK765R0-100E. 118 P5020NSE7VNB S12ZVML12EVBLIN SCC2692AC1N40 LPC1785FBD208K LPC2124FBD64/01 LS1020ASN7KQB LS1020AXN7HNB LS1020AXN7KQB LS1043ASE7PQA

